

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP628, TLP628-2, TLP628-4

Programmable Controllers

DC-Output Module

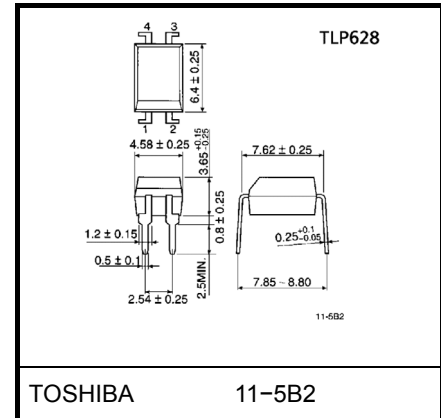
Telecommunication

The TOSHIBA TLP628, -2, and -4 consists of a gallium arsenide infrared emitting diode optically coupled to a phototransistor which has a 350V high voltage of collector-emitter breakdown voltage.

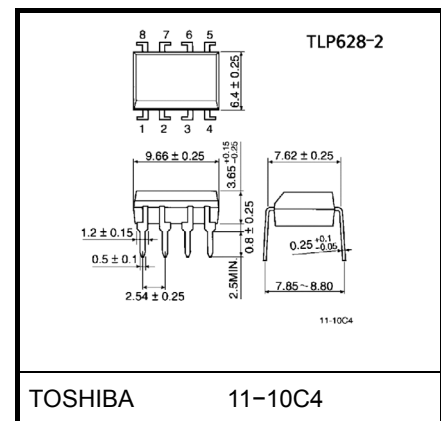
The TLP628-2 offers two isolated channels in a eight lead plastic DIP package, while the TLP628-4 provide four isolated channels per package.

- Collector-emitter voltage: 350 V (min.)
- Current transfer ratio: 50% (min.)
- Isolation voltage: 5000Vrms (min.)
- UL recognized: UL1577, file No. E67349
- BSI approved: BS EN60065:2002, certificate no.7426
BS EN60950-1:2002, certificate no.7427

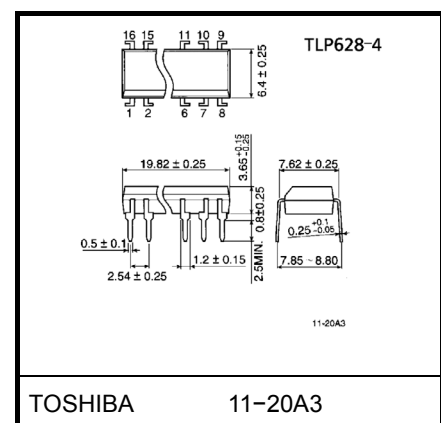
Unit in mm



Weight: 0.26g

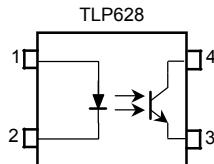


Weight: 0.54g

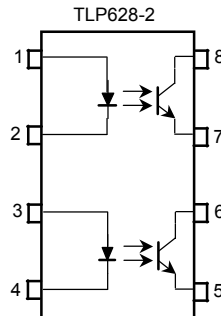


Weight: 1.1g

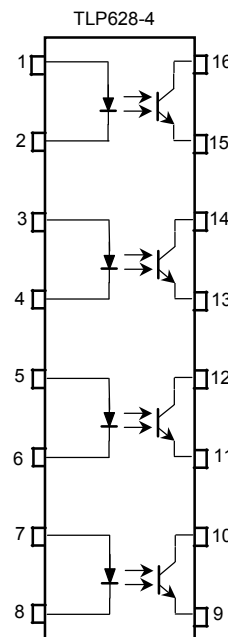
Pin Configurations (top view)



1: Anode
2: Cathode
3: Emitter
4: Collector



1, 3: Anode
2, 4: Cathode
5, 7: Emitter
6, 8: Collector



1, 3, 5, 7: Anode
2, 4, 6, 8: Cathode
9, 11, 13, 15: Emitter
10, 12, 14, 16: Collector

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating		Unit
			TLP628	TLP628-2 TLP628-4	
LED	Forward current	I_F	60	50	mA
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta $\geq 39^\circ\text{C}$)	-0.5 (Ta $\geq 25^\circ\text{C}$)	mA / $^\circ\text{C}$
	Pulse forward current	I_{FP}	1 (100 μs pulse, 100pps)		A
	Reverse voltage	V_R	5		V
	Junction temperature	T_j	125		$^\circ\text{C}$
Detector	Collector-emitter voltage	V_{CEO}	350		V
	Emitter-collector voltage	V_{ECO}	7		V
	Collector current	I_C	50		mA
	Collector power dissipation (1 circuit)	P_C	150	100	mW
	Collector power dissipation derating (Ta $\geq 25^\circ\text{C}$, 1 circuit)	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / $^\circ\text{C}$
	Junction temperature	T_j	125		$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~125		$^\circ\text{C}$
Operating temperature range		T_{opr}	-55~100		$^\circ\text{C}$
Lead soldering temperature		T_{sol}	260 (10s)		$^\circ\text{C}$
Total package power dissipation (1 circuit)		P_T	200	150	mW
Total package power dissipation derating (Ta $\geq 25^\circ\text{C}$, 1 circuit)		$\Delta P_T / ^\circ\text{C}$	-2.0	-1.5	mW / $^\circ\text{C}$
Isolation voltage		BV_S	5000 (AC, 1min., R.H. $\leq 60\%$) (Note 1)		Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	—	200	V
Forward current	I_F	—	16	25	mA
Collector current	I_C	—	—	10	mA
Operating temperature	T_{opr}	-25	—	85	$^\circ\text{C}$

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	I_R	$V_R = 5 \text{ V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR) \text{ CEO}}$	$I_C = 0.1 \text{ mA}$	350	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR) \text{ ECO}}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{\text{CE}} = 300 \text{ V}$	—	10	200	nA
			$V_{\text{CE}} = 300 \text{ V}, T_a = 85^\circ\text{C}$	—	—	50	μA
	Capacitance collector to emitter	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = 5 \text{ mA}, V_{\text{CE}} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1 \text{ mA}, V_{\text{CE}} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	$V_{\text{CE}} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

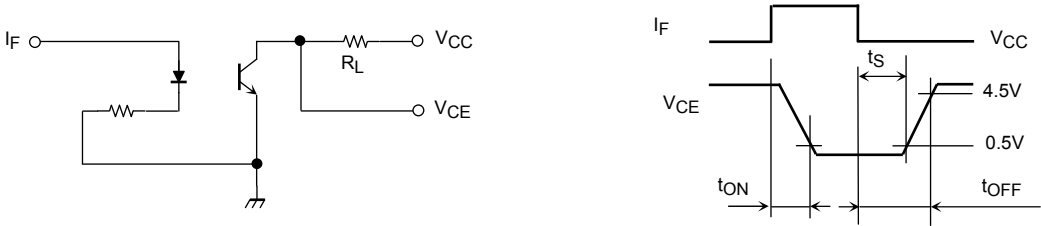
Isolation Characteristics (Ta = 25°C)

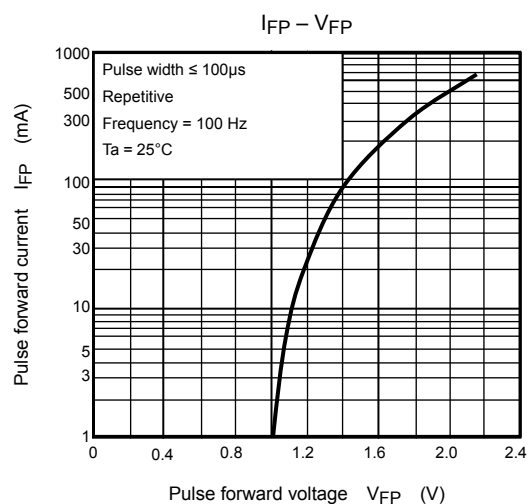
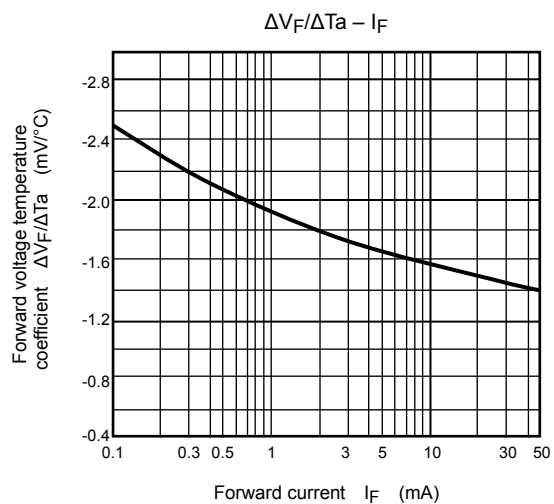
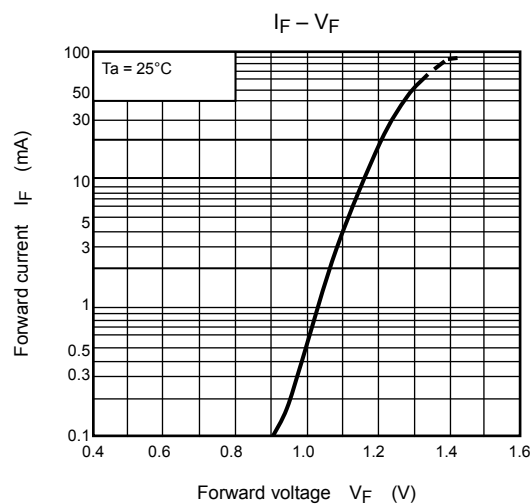
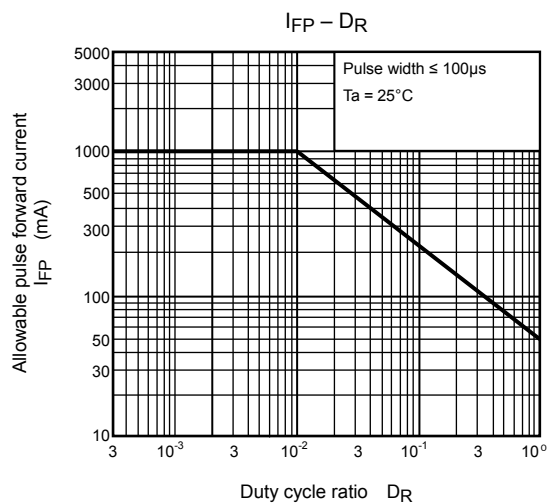
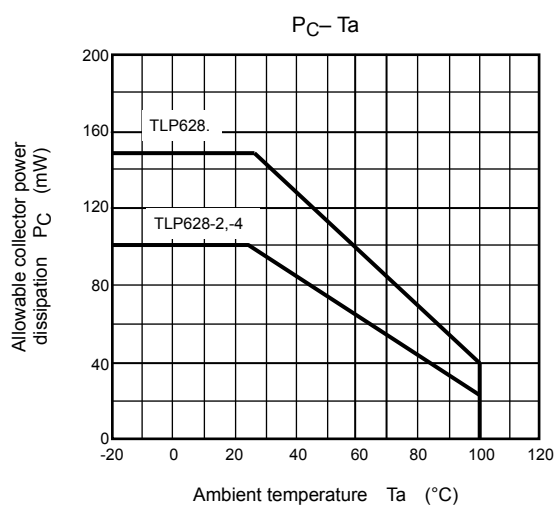
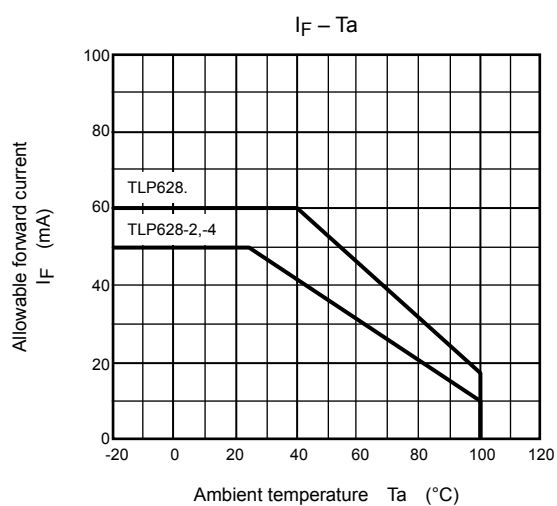
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C_S	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	—	pF
Isolation resistance	R_S	$V_S = 500 \text{ V R.H.} \leq 60\%$	5×10^{10}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	5000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V_{dc}

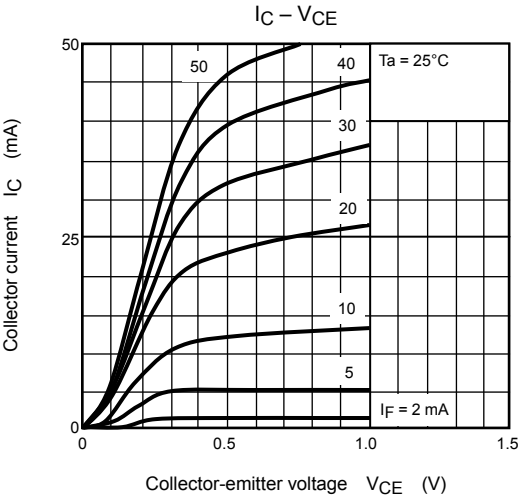
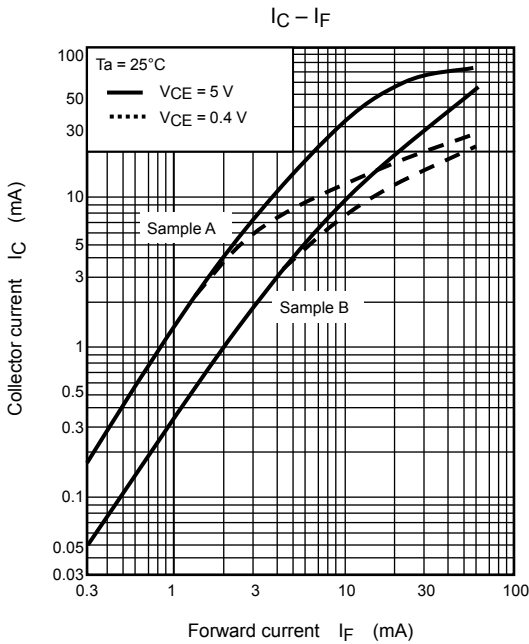
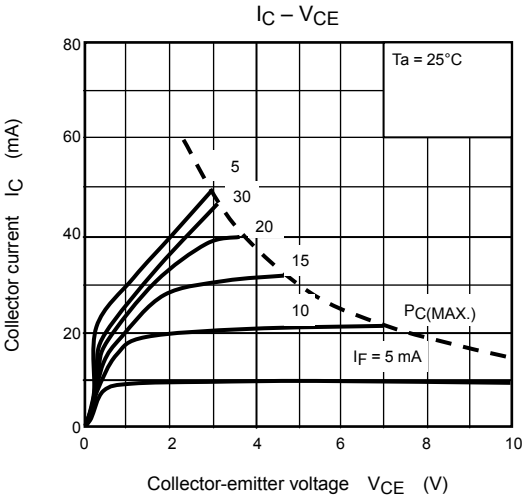
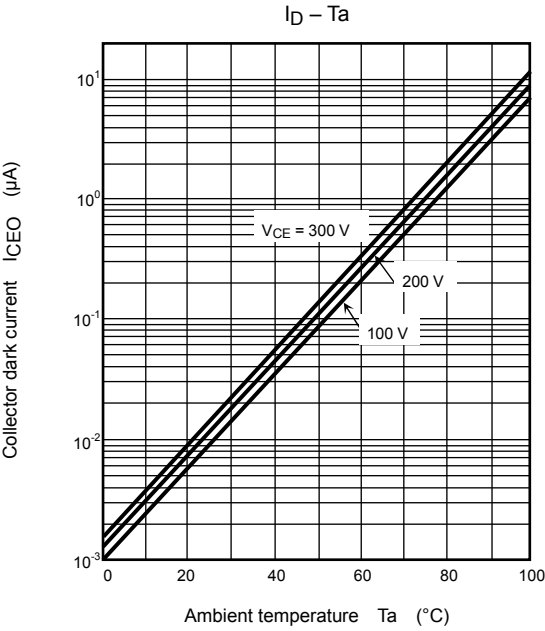
Switching Characteristics (Ta = 25°C)

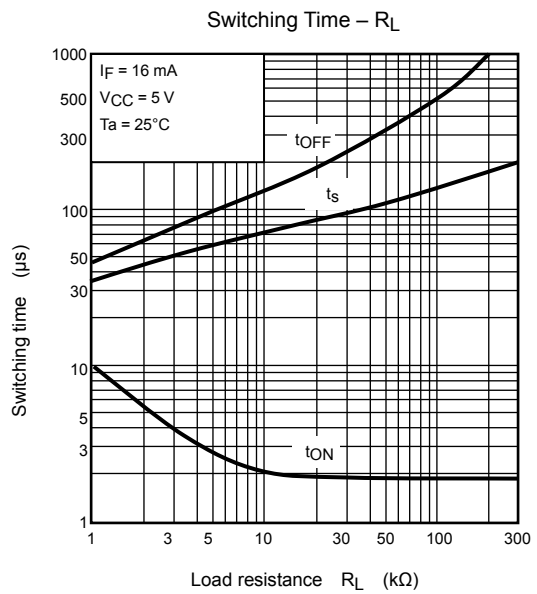
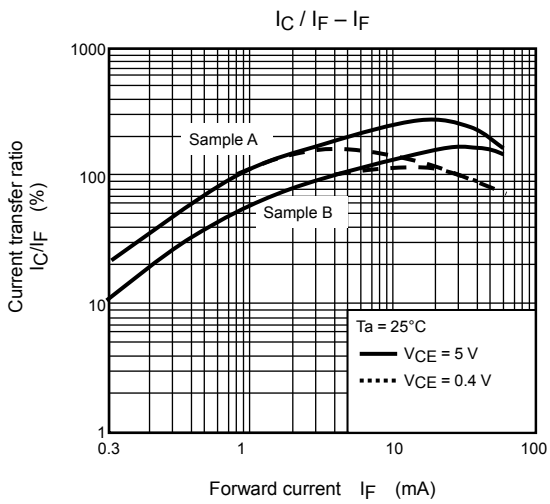
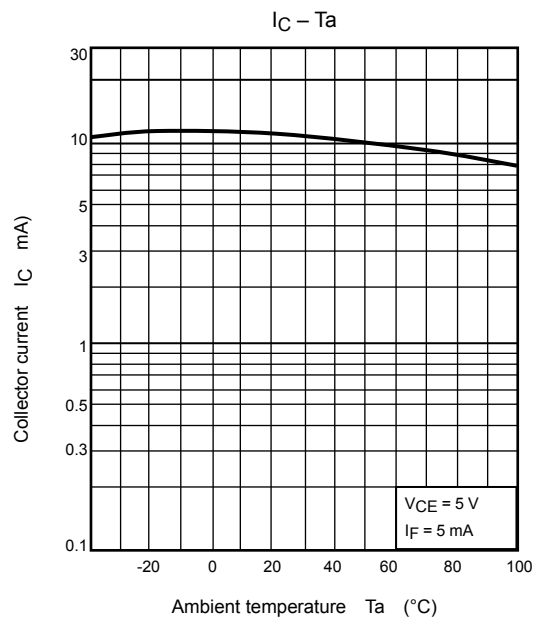
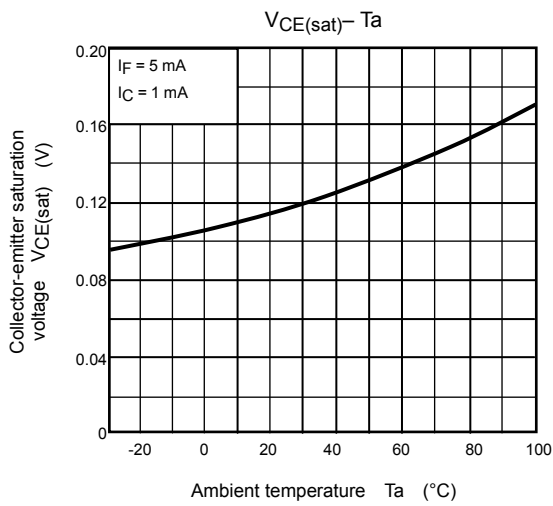
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t_r	$V_{CC} = 10\text{ V}, I_C = 2\text{ mA}$ $AR_L = 100\Omega$	—	2	—	μs
Fall time	t_f		—	3	—	
Turn-on time	t_{on}		—	3	—	
Turn-off time	t_{off}		—	3	—	
Turn-on time	t_{ON}	$R_L = 1.9\text{ k}\Omega$ (Fig.1) $V_{CC} = 5\text{ V}, I_F = 16\text{ mA}$	—	3	—	μs
Storage time	t_s		—	40	—	
Turn-off time	t_{OFF}		—	90	—	

Fig. 1 Switching time test circuit









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20070701-EN

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